Diode Semiconductor Device - Page 1 of 1



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Inclosure I	Materiai:
Glass	
Overall Le	ngth:
Between 0.	230 inches and 0.300 inches
Terminal L	.ength:
1.000 inche	es estas
Overall Dia	ameter:
Between 0.	.085 inches and 0.107 inches
End Applic	cation:
Tcn-500 (a	n/arn-15 (v))
Joint Elect	tronic Device Engineering Council/jedec/case Outline Designation:
Do-7	
Mounting I	Method:
Terminal	
Features P	Provided:
Hermeticall	ly sealed case
Semicond	uctor Material:
Silicon	
Voltage Ra	ating In Volts Per Characteristic:
33.0 regul	lator voltage
Current Ra	ating Per Characteristic:
0.250 millia	amperes reverse surge current
Power Rat	ing Per Characteristic:
250.0 milliv	vatts total power dissipation
Maximum	Operating Tempurature Per Measurement Point:
200.0 degre	ees celsius junction
Product Na	ame:
Semicondu	ictor device
Terminal T	Type And Quantity:
2 uninsulat	ed wire lead
Shelf Life:	
N/a	
Unit Of Me	easure:
Demilitariz	zation:
No	
Fiig:	
-	